PNP/NPN Epitaxial Planar Silicon Transistors



2SB1455/2SD2203

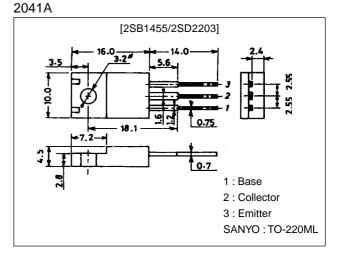
80V/7A High-Current Switching Applications

Features

- · Low collector-to-emitter saturation voltage.
- · Large current capacity.
- · Micaless package facilitating easy mounting.

Package Dimensions

unit:mm



():2SB1455

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		(–)90	V
Collector-to-Emitter Voltage	VCEO		(–)80	V
Emitter-to-Base Voltage	VEBO		(-)6	V
Collector Current	ι _C		()7	A
Collector Current (Pulse)	ICP		(–)12	A
Collector Dissipation	PC		2.0	W
		Tc=25°C	30	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

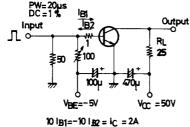
Parameter	Symbol		Conditions							Unit			
Falanielei	Symbol	Conditions						min	typ	max	Onit		
Collector Cutoff Current	ICBO	V _{CB} =(-)80V, I _E =0 (-)0.1							()0.1	mA			
Emitter Cutoff Current	IEBO	V _{EB} =(-)4V, I _C =0 (-)							()0.1	mA			
DC Current Gain	h _{FE} 1	V _{CE} =(-)2V, I _C =(-)1A							70	e .	280*		
	h _{FE} 2	V _{CE} =(-)2V, I _C =(-)4A							30)			
Gain-Bandwidth Product	fT	V _{CE} =(-)5V, I _C =(-)1A 20							MHz				
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =(-)4A, I _B =(-)0.4A						0.4	V				
										(-0.5)	V		
* : The 2SB1455/2SD2203 are classified by 1A h_{FE} as follows :			70 Q	140	100	R	200	140	S	280			

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SANYO Electric Co., Ltd. Semiconductor Bussiness Headquaters TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

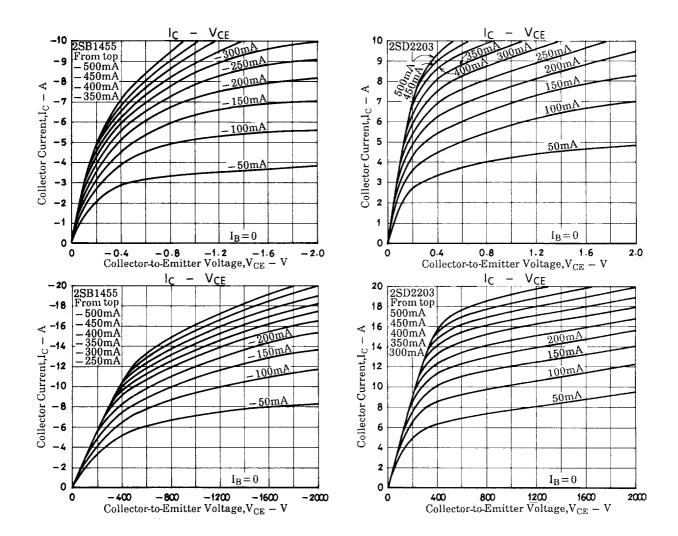
Parameter	Symbol	Conditions		Unit		
Falameter	Symbol	Conditions	min	typ	max	Unit
Collector-to-Base Breakdown Voltage	V _(BR) CBO	I _C =(-)1mA, I _E =0	(–)90			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =(–)1mA, R _{BE} =∞	(–)80			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =(-)1mA, I _C =0	()6			V
Turn-ON Time	ton	See specified test circuit.		(0.2)		μs
				0.1		μs
Storage Time	tstg	See specified test circuit.		(0.7)		μs
				1.6		μs
Fall Time	t _f	See specified test circuit.		(0.2)		μs
				0.4		μs

Switching Time Test Circuit

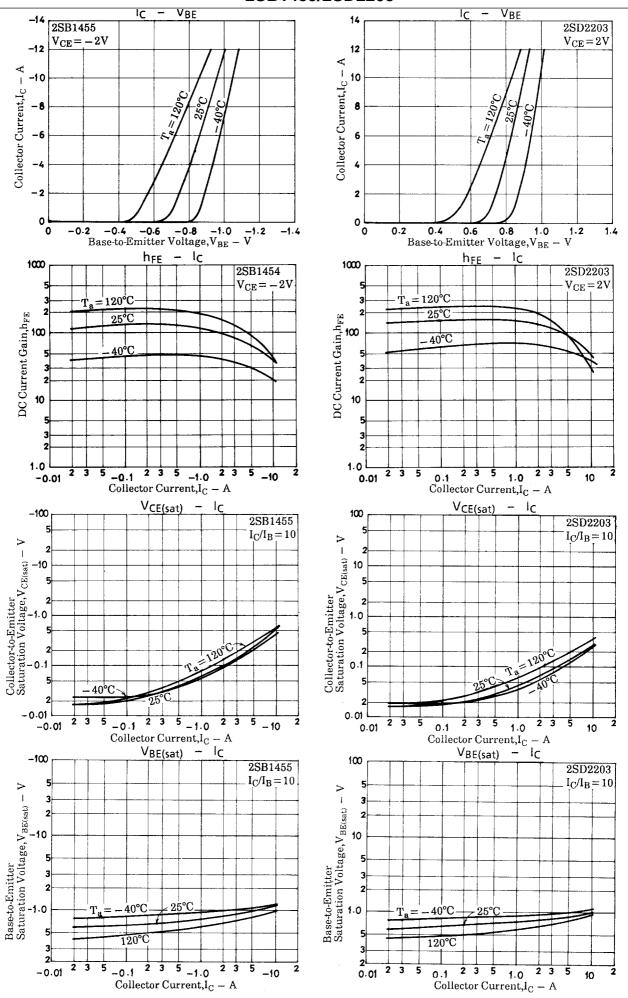


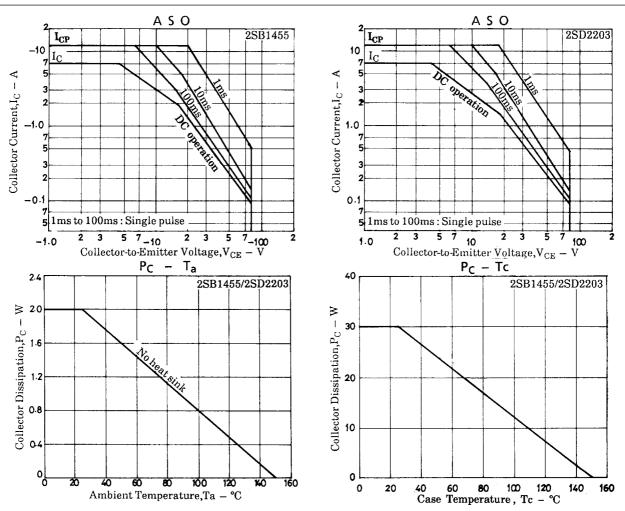
For PNP, the polarity is reversed.

Unit (resistance : Ω , capacitance : F)



2SB1455/2SD2203





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